

# New approach to MoSi<sub>2</sub>/SiC intermetallic-ceramic composite with B<sub>4</sub>C

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The effects of SiC and B<sub>4</sub>C additives in the MoSi<sub>2</sub> matrix on the microstructures and mechanical properties at room temperature were investigated. Their coefficients of thermal expansion (CTE) were also evaluated up to 1200°C by a thermal mechanical analysis (TMA). The experimental results show that the Mo<sub>2</sub>B<sub>5</sub> reinforced phase was formed *in situ* in the hot-pressed MoSi<sub>2</sub>/SiC/B<sub>4</sub>C composites. Both the Mo<sub>2</sub>B<sub>5</sub> phase and the SiC phase significantly improved the mechanical behavior of MoSi<sub>2</sub>. Besides, the SiC with a high content up to 40 vol% could be added into the MoSi<sub>2</sub> composite with the B<sub>4</sub>C additive. As a result, a dense and homogenous MoSi<sub>2</sub>/SiC/B<sub>4</sub>C composite was obtained, which possessed a relatively high bending strength and fracture toughness. Meanwhile, the CTE of the MoSi<sub>2</sub>/SiC/B<sub>4</sub>C composites linearly decreased with the increasing SiC content, which dropped to 21% at 1200°C in comparison with the pure MoSi<sub>2</sub> when adding 40 vol% SiC. This MoSi<sub>2</sub>/SiC/B<sub>4</sub>C composite system is very important for developing new applications at elevated temperature, particularly for high-temperature coating applications.

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## 1. Introduction

MoSi<sub>2</sub> has been widely utilized as a high-temperature structural component and the high-temperature protective coatings in the aerospace field, heating elements in thermal treatment technology, and the conductors of integrated circuits in the microelectronic technology due to its high melting point (2030°C), excellent oxidation and corrosion resistance, high electrical conductivity, reasonable density (6.31 g/cm<sup>3</sup>), and improvable mechanical properties. MoSi<sub>2</sub> has excellent high-temperature properties. It can be used at temperatures up to 1500°C for a long time, and up to 1700°C for a short time due to the formation of a protective silica film on the MoSi<sub>2</sub> surface at elevated temperature [1, 2]. MoSi<sub>2</sub> is easily shaped at high temperature due to its good ductile property, but it is difficult at room temperature because of its brittle property caused by an insufficient slip system of the polycrystalline MoSi<sub>2</sub> similar to most intermetallics [3]. Unfortunately, the mechanical properties of the pure MoSi<sub>2</sub> are not sufficient above room temperature. Hence, till now, many elements and compounds have been used to reinforce its mechanical properties and to improve the oxidation-resistance of MoSi<sub>2</sub>, such as the single elements (Al, Ti, Ta, Ni, B, C), oxides (Sc<sub>2</sub>O<sub>3</sub>, Y<sub>2</sub>O<sub>3</sub>, Al<sub>2</sub>O<sub>3</sub>, ZrO<sub>2</sub>, B<sub>2</sub>O<sub>3</sub>), nitrides (Si<sub>3</sub>N<sub>4</sub>), carbides (SiC, TiC), and borides (TiB<sub>2</sub>) [4–13]. Among them, adding 20 vol%

SiC into MoSi<sub>2</sub> is considered to be the most effective, which significantly strengthened the mechanical properties and creep resistance of MoSi<sub>2</sub> meanwhile, no cracks are observed at the MoSi<sub>2</sub>/SiC interface [14].

Most studies on MoSi<sub>2</sub> are aimed at improving its structures and mechanical properties. In fact, it is very important to eliminate the thermal expansion mismatch between the MoSi<sub>2</sub> and the other structural ceramic components at elevated temperature because MoSi<sub>2</sub> has a much higher CTE than the general structural ceramics (such as the Si<sub>3</sub>N<sub>4</sub>). Besides, the MoSi<sub>2</sub> composite with a low CTE is very useful for the development of the MoSi<sub>2</sub> composite coating on the Mo and Nb alloys, and even on ceramic materials.

Based on above consideration, this research aims to decrease the CTE of the MoSi<sub>2</sub> composite by increasing the volume content of SiC as well as to improve the mechanical properties of the MoSi<sub>2</sub> composite. Boron and carbon are generally used in reinforcing the mechanical properties of MoSi<sub>2</sub> [8, 15], and B<sub>4</sub>C is a normal additive in the sintering process of SiC ceramics. From this point of view, B<sub>4</sub>C (2.51 g/cm<sup>3</sup>) was chosen as another additive to promote the compatibility between the MoSi<sub>2</sub> and SiC for the purpose of fabricating the MoSi<sub>2</sub>/SiC/B<sub>4</sub>C composites with an excellent mechanical property and with a low CTE. To the best of our knowledge, this material system, the MoSi<sub>2</sub>/SiC

composite reinforced by B<sub>4</sub>C, has not been reported so far.

## 2. Experimental

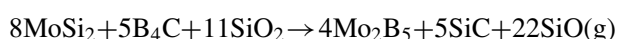
The MoSi<sub>2</sub> composites with 0.5, 1.0, 2.0, and 4.6 wt% B<sub>4</sub>C and 20, and 40 vol% SiC were fabricated by hot-pressing (30 MPa) in an argon atmosphere (0.1 MPa). Their compositions and preparation conditions are listed in Table I. The raw materials were MoSi<sub>2</sub> powders of 2–5 μm (99%, New Metals, Japan), β-SiC powders of 0.29 μm (99%, Ibiden, Japan), and B<sub>4</sub>C powders of 10 μm (99%, Kempton Electric Melting Plant, Germany). The powders were milled for 24 hours with SiC balls in methanol. After mixing, drying and sieving, they were hot-pressed into a bulk with a size of 40 × 40 × 5 mm at 1650°C–1750°C. The hot-pressing temperature was measured by monitoring the temperature of the graphite die using a two-color pyrometer. The surface of the graphite die that touched the sample was coated with boron nitride powder to prevent them from sticking together. The compressive stress exerted upon the sample was removed at the beginning of cooling in the hot-pressing in order to decrease the residual stress in the sample.

A phase analysis of the composites was performed by X-ray diffraction (XRD) (Model Dmax 3A, Rigaku, Japan) with a Cu target (40 kV, 20 mA) and graphite monochromator. An optical microscope and scanning electron microscopy (SEM) technique with energy-dispersive X-ray analysis (EDAX) were used to observe the microstructures and analyze their chemical compositions. The density measurement was based on Archimedes' principle. The coefficients of thermal expansion were measured up to 1200°C using a thermal mechanical analysis (Model TMA 8140, Rigaku, Japan) with a thermal analysis station (Model TAS100, Rigaku, Japan). Samples for the three-point bending strength measurements were machined to dimension of 36 × 4 × 3 mm. The down span of the measurement was 30 mm and the speed of the crosshead was 0.5 mm/min. Samples for the four-point fracture toughness measurement were machined to 36 mm long, 3 mm wide and 4 mm thick with the notch length of about 1.5 mm and crack tip radii of 0.10 mm. The up span was 10 mm, the down one was 30 mm, and the speed of the crosshead was 0.1 mm/min. The Vickers hardness was measured by a Akashi microhardness tester (Model

MVK-E, Akashi, Japan) under the load of 1.96 N. The surface of the samples was ground using an 800-mesh diamond-grinding wheel.

## 3. Results and discussion

Fig. 1 shows the XRD patterns of the pure MoSi<sub>2</sub> and MoSi<sub>2</sub>/SiC/B<sub>4</sub>C composites with various compositions. The pure MoSi<sub>2</sub> (sample 1) possessed a single tetragonal phase. Both the MoSi<sub>2</sub> and SiC phases were observed in the MoSi<sub>2</sub>/SiC composite because they are thermodynamically stable at elevated temperature in the phase diagram [16]. The XRD patterns show that the relative intensities of SiC peaks were enhanced by increasing SiC content for the same B<sub>4</sub>C content. This was induced by the SiC itself. However, the SiC phase was observed after adding the 4.6 wt% B<sub>4</sub>C into the MoSi<sub>2</sub> matrix without any addition of SiC (as shown in the curve of sample 2 in Fig. 1). The appearance of the SiC phase in the MoSi<sub>2</sub>/B<sub>4</sub>C composite was probably caused by the following reaction:



As already mentioned, the silica always exists in MoSi<sub>2</sub> at high temperature. It is very harmful for the creep resistance of the MoSi<sub>2</sub> due to its low melting point. This reaction led to a reduction of the silica in the MoSi<sub>2</sub>. It was of benefit to improve the mechanical properties

TABLE I Preparation of hot-pressed MoSi<sub>2</sub> composites

Sample no.	SiC content (vol%)	B <sub>4</sub> C content (wt%)	Hot-pressing temp. (°C)
1	0	0	1650
2	0	4.6	1650
3	20	0	1750
4	20	1.0	1650
5	20	2.0	1650
6	20	4.6	1650
7	40	0.5	1700
8	40	1.0	1700
9	40	2.0	1700
10	40	4.6	1700

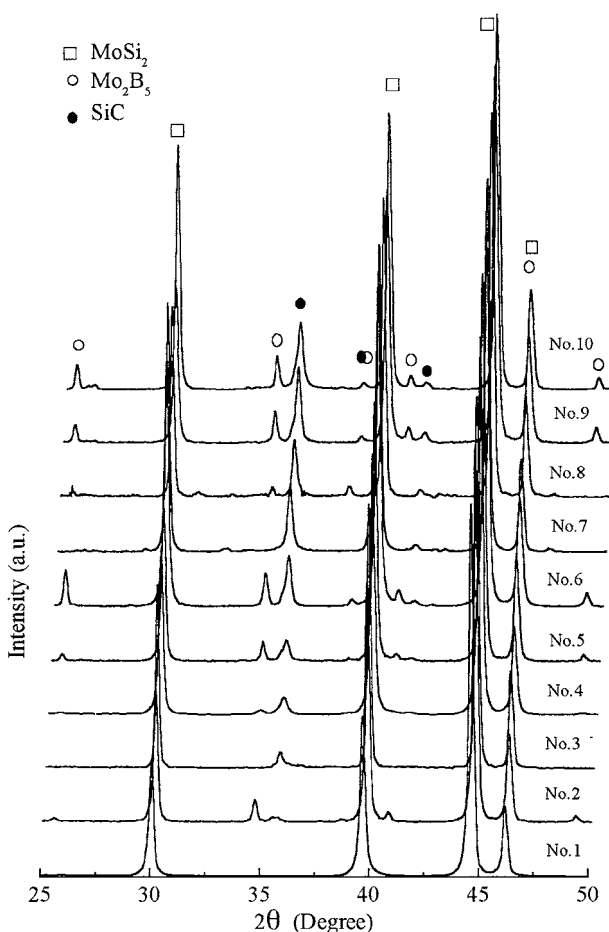


Figure 1 XRD patterns of pure MoSi<sub>2</sub> and MoSi<sub>2</sub>/SiC/B<sub>4</sub>C composites (from sample 1 to 10).

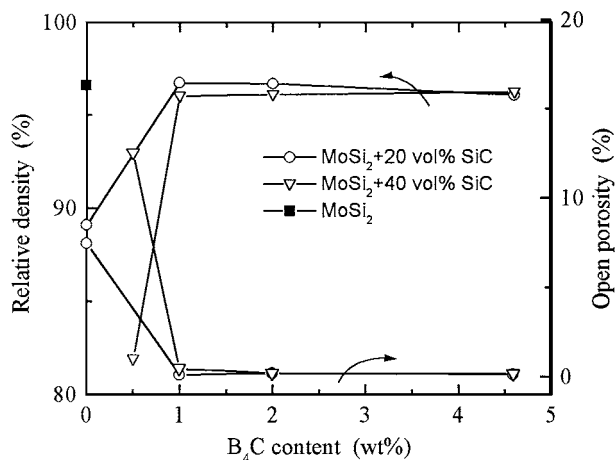


Figure 2 Densities of the MoSi<sub>2</sub>/SiC/B<sub>4</sub>C composites.

of the MoSi<sub>2</sub>. Simultaneously, it is worthy noting that the relative intensity of the SiC peaks in XRD patterns was also strengthened with increasing the B<sub>4</sub>C content for same SiC content. This result further confirmed the existence of the above solid-state reaction in the MoSi<sub>2</sub>-B<sub>4</sub>C material system. On the other hand, it was of interest that a new Mo<sub>2</sub>B<sub>5</sub> phase was found in the MoSi<sub>2</sub>, MoSi<sub>2</sub>/SiC composites with B<sub>4</sub>C except for MoSi<sub>2</sub>/SiC with 0.5 wt% B<sub>4</sub>C (perhaps the amount was not enough to be observed by the XRD). The relative intensity of the Mo<sub>2</sub>B<sub>5</sub> peaks increased with the increasing B<sub>4</sub>C content. The effect of the Mo<sub>2</sub>B<sub>5</sub> phase on the mechanical property and thermal expansion of the MoSi<sub>2</sub> composite will be discussed later.

From the experimental results, the relative density of the MoSi<sub>2</sub>/B<sub>4</sub>C composite (4.6 wt% B<sub>4</sub>C) increased up to 97.76% from the pure MoSi<sub>2</sub> of 96.60% after hot-pressed at 1650°C. The pure MoSi<sub>2</sub>/SiC composites (20 vol% SiC) exhibited a poor density of 89.12% even if the sintering temperature was raised up to 1750°C. By adding the proper B<sub>4</sub>C content, the relative densities of the MoSi<sub>2</sub>/SiC composites were greatly increased as shown in Fig. 2. As a consequence, most MoSi<sub>2</sub>/SiC composites with B<sub>4</sub>C additive were basically the same as the pure MoSi<sub>2</sub> in relative density. This indicates that the proper amount of B<sub>4</sub>C could effectively improve the density of the MoSi<sub>2</sub> composites. Besides, for the MoSi<sub>2</sub> composites with the 20 vol% SiC additive, the relative density increased with the increasing B<sub>4</sub>C content at the beginning, and then reached a maximum value, followed by a slow decrease. The relative density of the MoSi<sub>2</sub> composites with 40 vol% SiC remained unchanged with the increasing B<sub>4</sub>C content after attaining the maximum value. The open porosity of the composites was contrary to the corresponding density as shown in Fig. 2. According to the above discussion, the perfect relative density could be obtained by adding above 1.0 wt% B<sub>4</sub>C into the MoSi<sub>2</sub> composites along with SiC of 20 vol% and 40 vol%.

Fig. 3 shows the optical microscope photographs of the pure MoSi<sub>2</sub> and MoSi<sub>2</sub>/SiC/B<sub>4</sub>C composites. They were observed after etching in the solution with a volume ratio of HNO<sub>3</sub> : HF : H<sub>2</sub>O = 2 : 1 : 5 at room temperature. The pure MoSi<sub>2</sub> had a single phase with a small silica phase that appeared in the photograph in

the form of small black dots as shown in Fig. 3a. The other samples consisted of several phases that were uniformly distributed in the composites. The existence of the second-enforcement phase, Mo<sub>2</sub>B<sub>5</sub>, was confirmed by the EDAX analysis. This Mo<sub>2</sub>B<sub>5</sub> phase was formed *in situ* during the hot-pressing of the MoSi<sub>2</sub>-B<sub>4</sub>C composites at 1650–1700°C. It obviously blocked the growth of the MoSi<sub>2</sub> grains, so that the grain size of the MoSi<sub>2</sub> decreased with the increasing SiC and B<sub>4</sub>C contents. The ultrafine microstructure was also found in the MoSi<sub>2</sub> composite with 40 vol% SiC and 4.6 wt% B<sub>4</sub>C (Fig. 3h). Generally, the formation of silica will weaken the mechanical properties of the MoSi<sub>2</sub>. However, the silica phase was not found in the MoSi<sub>2</sub>/SiC/B<sub>4</sub>C composites based on the EDAX analysis. This indicates that the existence of the Mo<sub>2</sub>B<sub>5</sub> phase hindered the formation of silica from the MoSi<sub>2</sub> matrix. Moreover, the appearance of the Mo<sub>2</sub>B<sub>5</sub> phase would promote improvement of the mechanical properties of the MoSi<sub>2</sub> composites as reported by Watanabe and coworkers [17], who chose Mo<sub>2</sub>B<sub>5</sub> as the reinforcement phase to improve the mechanical properties and oxidation-resistance of MoSi<sub>2</sub>. The *in situ* formation of this reinforced phase also avoided the mismatch between the matrix and the additive phase, thus leading to improvement of the mechanical properties [7, 16, 18]. Therefore, the Mo<sub>2</sub>B<sub>5</sub> reinforced phase played an important role in adjusting the properties of MoSi<sub>2</sub>. Besides, a small SiC phase was observed by EDAX in the MoSi<sub>2</sub>/B<sub>4</sub>C composite without the SiC additive, which was consistent with the XRD analysis detailed above. A little Si-B phase was also found in the composites. The formation of this glass-like phase favored to raise the creep ratio at elevated temperature.

The CTE curves of the various MoSi<sub>2</sub> composites are presented in Fig. 4. The CTE increased with the increasing temperature and the addition of SiC could effectively decrease the CTE. In comparison with the pure MoSi<sub>2</sub>, the CTE of the composites dropped 21% at 1200°C. The lowest CTE could be achieved in the MoSi<sub>2</sub> composite with the co-addition of 40 vol% SiC and 4.6 wt% B<sub>4</sub>C. Fig. 5 shows the CTE change of the MoSi<sub>2</sub>/SiC composites with 1.0 wt% B<sub>4</sub>C at 1200°C, which was situated between the pure MoSi<sub>2</sub> and SiC, and linearly reduced with the increasing SiC content. However, the B<sub>4</sub>C additive had only a slight influence on the CTE in these composites by comparison with the SiC additive. This implied that the change in the CTE mainly depended on the change in the SiC content.

Fig. 6 shows the mechanical properties of the MoSi<sub>2</sub> composites at room temperature. Obviously, the microhardness of the MoSi<sub>2</sub> composites was much higher than that of the pure MoSi<sub>2</sub> and in proportion to the contents of SiC and B<sub>4</sub>C. As stated in the above discussion of the XRD analysis, the SiC and B<sub>4</sub>C additives induced the SiC and Mo<sub>2</sub>B<sub>5</sub> phases in the MoSi<sub>2</sub> matrix. The hardness of both SiC and Mo<sub>2</sub>B<sub>5</sub> is much higher than MoSi<sub>2</sub>. They are 19 GPa, 23 GPa and 9 GPa, respectively [7]. Accordingly, a high hardness can be achieved in the MoSi<sub>2</sub> composites with SiC and B<sub>4</sub>C additives.

The bending strength and fracture toughness of the MoSi<sub>2</sub> composites were also investigated at room

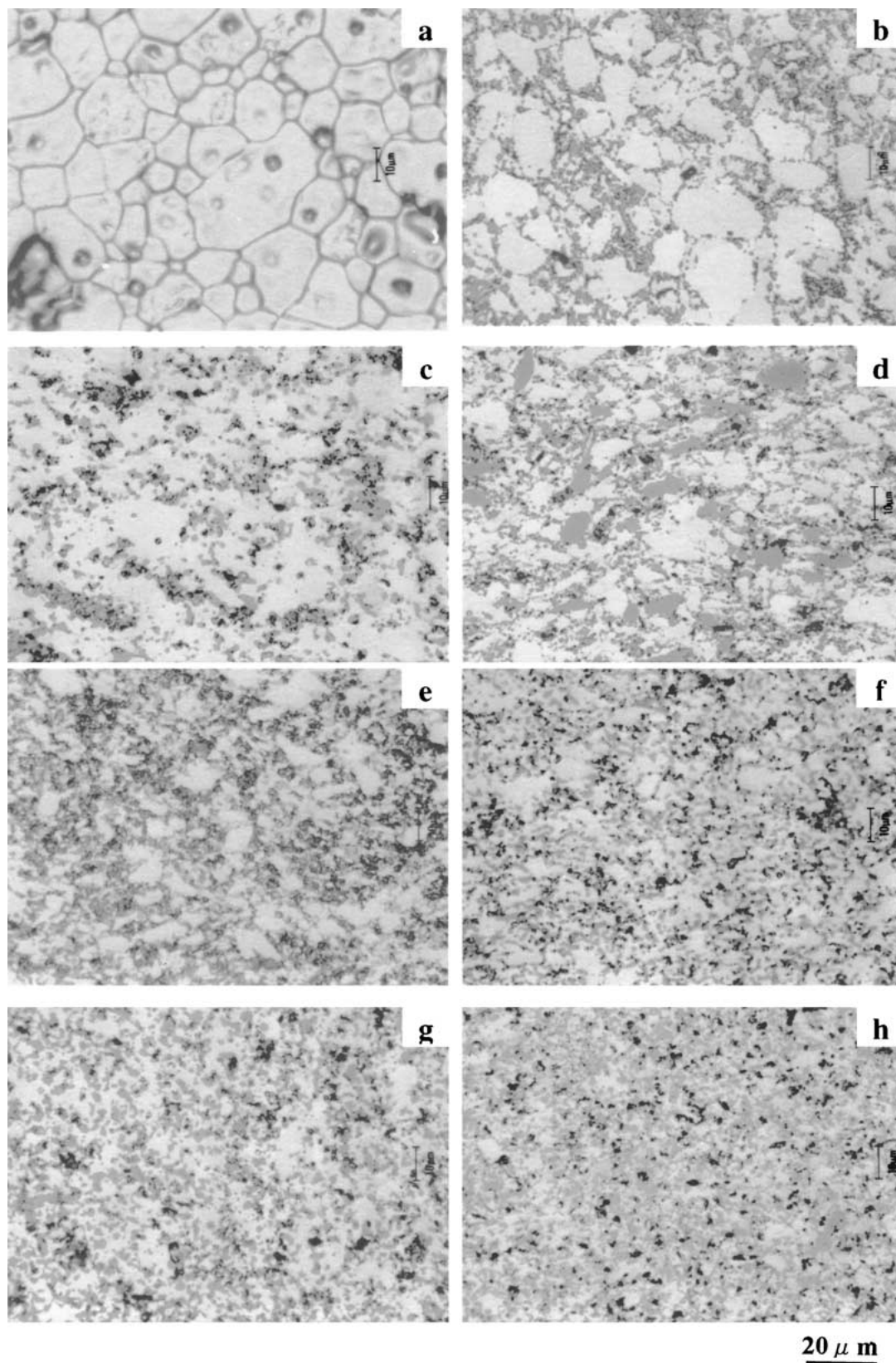


Figure 3 Optical microscope photos of pure MoSi<sub>2</sub> and MoSi<sub>2</sub>/SiC/B<sub>4</sub>C composites: a(sample 1); b–d(sample 4–6); and e–h(sample 7–10).

temperature. As a result, the bending strength and fracture toughness of the composites were significantly higher than the pure MoSi<sub>2</sub> (345.9 MPa, 4.27 MPa · m<sup>-1/2</sup>, respectively). Among them, the effect of the SiC additive on the mechanical properties was more significant than the B<sub>4</sub>C additive. This is in agreement with the effect of the additive on the CTE discussed above. The maximum bending strength

reached 710 MPa for the MoSi<sub>2</sub> composite with 40 vol% SiC and 1.0 wt% B<sub>4</sub>C. Correspondingly, the maximum fracture toughness appeared in the MoSi<sub>2</sub> composite with 40 vol% SiC and 4.6 wt% B<sub>4</sub>C, which is about 7 MPa m<sup>1/2</sup>. This suggests that the SiC plays an important role in the improvement of the bending strength and the fracture toughness. It is also noted that the B<sub>4</sub>C content should be carefully controlled since the *in situ*

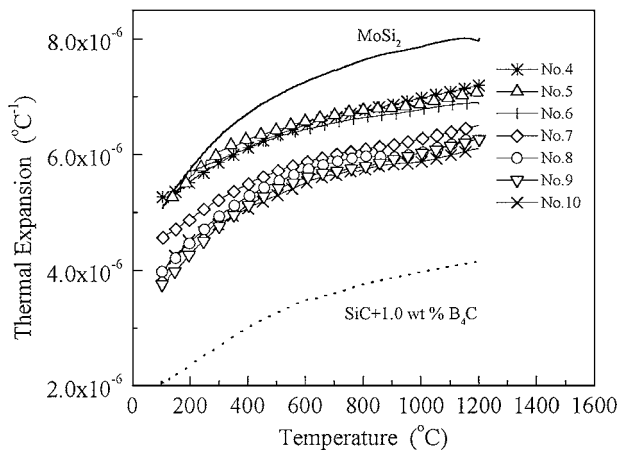


Figure 4 The CTE curves of various MoSi<sub>2</sub> composites.

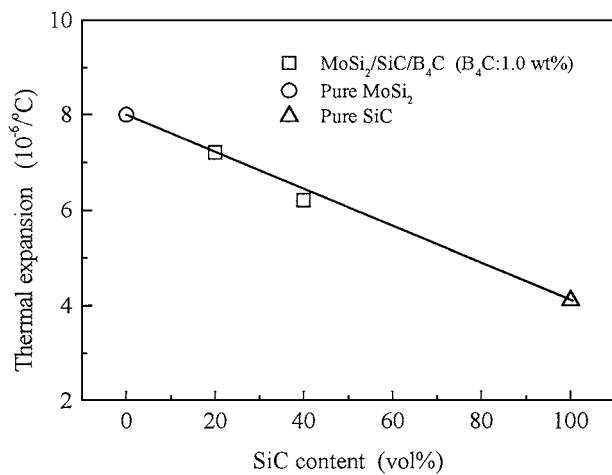


Figure 5 The CTE as a function of the SiC content at 1200°C.

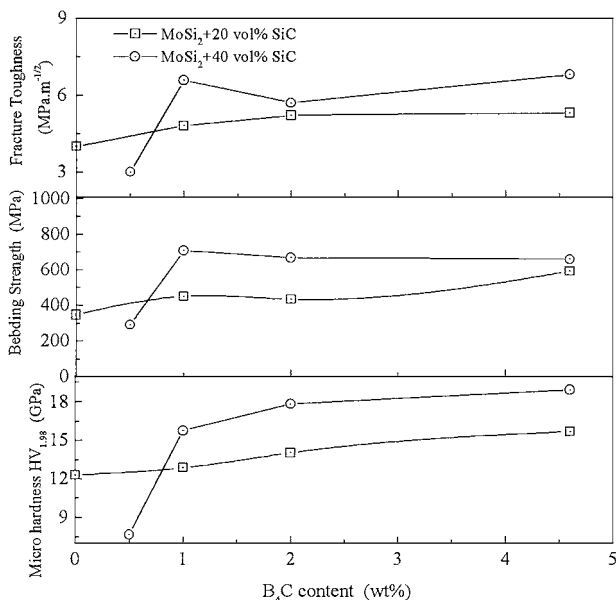


Figure 6 The mechanical properties of various MoSi<sub>2</sub> composites.

formation of Mo<sub>2</sub>B<sub>5</sub> during the hot-pressing process of MoSi<sub>2</sub>/SiC/B<sub>4</sub>C favored the improvement in the mechanical properties of the composites at room temperature, but too much Mo<sub>2</sub>B<sub>5</sub> would result in the poor oxidation-resistance at elevated temperature in an oxygen atmosphere [17]. In conclusion, the additive content

in the range of 40 vol% SiC and about 1.0 wt% B<sub>4</sub>C should be a promising composition for this material system.

#### 4. Conclusions

The second-reinforcement Mo<sub>2</sub>B<sub>5</sub> phase was successfully formed *in situ* during the hot-pressing process in the MoSi<sub>2</sub> composites with SiC and B<sub>4</sub>C. As a result, a dense and homogenous MoSi<sub>2</sub> composite with 40 vol% SiC was obtained by adding about 1.0 wt% B<sub>4</sub>C. The SiC additive significantly increased the mechanical properties and decreased the CTE of the MoSi<sub>2</sub> composite. The B<sub>4</sub>C additive promoted the formation of the second-reinforcement Mo<sub>2</sub>B<sub>5</sub> in the MoSi<sub>2</sub> composites, thus leading to an increase in the microhardness and reduction in the CTE. Typically, the microhardness, the bending strength and fracture toughness of the MoSi<sub>2</sub> composite with 40 vol% SiC and 1.0 wt% B<sub>4</sub>C reached 16.5 Gpa, 710 Mpa and 6.3 MPa<sup>1/2</sup>, respectively. The CTE of this composite dropped 21% in comparison with the pure MoSi<sub>2</sub> at 1200°C. This illustrates that this MoSi<sub>2</sub>/SiC/B<sub>4</sub>C system possesses excellent mechanical properties and a low CTE, and can be used as high temperature elements as well as high-temperature coating materials.

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#### References

1. A. K. VASUDEVAN and J. J. PETROVIC, *Mater. Sci. Eng. A* **155** (1992) 1.
2. X. FAN, T. ISHIGAKI, Y. SUETSUGU, J. TANATA and Y. SATO, *J. Amer. Ceram. Soc.* **81** (1998) 2517.
3. D. J. EVANS, *Phil. Mag.* **75** (1997) 1.
4. M. K. MEYER, A. J. THOM and M. AKINC, *Intermetallics* **7** (1999) 153.
5. K. YANAGIHARA, T. MARUYAMA and K. NAGATA, *ibid.* **3** (1995) 243.
6. J. J. PETROVIC, *Mater. Sci. Eng. A* **192/193** (1995) 31.
7. A. COSTA E SILVA and M. J. KAUFMAN, *Mater. Sci. Eng. A* **195** (1995) 75.
8. *Idem.*, *Intermetallics* **5** (1997) 1.
9. J.-M. TING, *J. Amer. Ceram. Soc.* **77** (1994) 2751.
10. Y. SUZUKI, P. E. D. MORGAN and K. NIIHARA, *ibid.* **81** (1998) 3141.
11. J. SUBRAHMANYAM and R. MOHAN RAO, *J. Mater. Res.* **10** (1995) 1226.
12. H. KUNG, Y. C. LU, A. H. BARTLETT, R. G. CASTRO and J. J. PETROVIC, *ibid.* **13** (1998) 1522.
13. K. TANAKA, K. NAWATA, H. INUI, M. YAMAGUCHI and M. KOIWA, *Intermetallics* **6** (1998) 607.
14. Y. SUZUKI and K. NIIHARA, *ibid.* **6** (1998) 7.
15. K. NIIHARA and Y. SUZUKI, *Mater. Sci. Eng. A* **261** (1999) 6.
16. C. M. WARD-CLOSE, R. MINOR and P. J. DOORBAR, *Intermetallics* **4** (1996) 217.
17. T. WATANABE and K. SHOBU, *MRS Int. Mtg. On Adv. Mats.* **7** (1989) 303.
18. X. FAN, T. ISHIGAKI and Y. SATO, *J. Amer. Ceram. Soc.* **82** (1999) 281.

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